

IN THE CLAIMS:

Please amend claim 1 as follows. This listing of the claims replaces prior listings of the claims in this case.

Claim 1 (Currently amended): A method for fabricating a semiconductor device, comprising the steps of:

sequentially forming a gate insulating film and a conductive layer for a gate electrode on a semiconductor substrate;

forming a multi-layered hard mask layer on the conductive layer, ~~wherein the multi-layered hard mask layer includes a stacked structure of nitride film/oxide film/nitride film;~~

etching the hard mask layer, the conductive layer and the gate insulting film using a gate electrode mask to form a stacked structure of a gate insulating film pattern, a gate electrode and a hard mask layer pattern serving as a gate pattern;

forming an insulating film spacer on a sidewall of the stacked structure;

forming an interlayer insulating film on the entire surface;

etching the interlayer insulating film using a landing plug contact etching mask to form a landing plug contact hole exposing the semiconductor substrate;

forming a conductive layer for a landing plug on the entire surface so as to fill the landing plug contact hole; and

planarizing the conductive layer for a landing plug to form a landing plug,

wherein the multi-layered hard mask layer includes a stacked structure of nitride film/oxide film/nitride film serving as a barrier layer during the etching process for a gate pattern.

Claim 2 (Cancelled).